

Letters

Influence of hydrostatic pressure on the microstructure of LiF single crystals containing cavities

When a solid containing elastic discontinuities is subjected to an external hydrostatic pressure, local shear stresses may be induced in the vicinity of these interfaces or boundaries [1]. Changes in microstructure and accompanying effects on the mechanical properties have been reported in cubic-metal and ionic crystals containing precipitate particles or grain boundaries [1-6] following pressurization in the range 3 to 30 kbar. It is generally accepted that dislocations are generated when locally the shear stress attains the value of the theoretical shear strength of the matrix. The purpose of this communication is to report generation of dislocations by hydrostatic pressure in LiF containing cavities.

Specimens of approximate dimensions $2 \times 2 \times 10$ mm were cleaved along $\{100\}$ planes from nominally pure single crystal LiF. To produce the cavities samples were irradiated to an integrated neutron flux of 5 or 8×10^{16} nvt, annealed for 20 h at 800°C and furnace cooled.

Examination of the as-cooled material revealed the presence of small rectangular voids, described in detail by, e.g. Gilman and Johnston [7]. The cavities, whose sides were composed of $\{100\}$ planes, displayed a wide variation in aspect ratio; dimensions of their sides being approximately in the range 10^{-1} to $10^2 \mu\text{m}$. Etching of the $\{100\}$ faces in H_2O_2 showed that the majority of the voids were associated with low angle boundaries; the cavities within the subgrains, however, were completely dislocation free. The mean dislocation density in the as-cooled state was approximately $2 \times 10^5 \text{cm}^{-2}$.

Examination of etched $\{100\}$ faces following pressurization treatments in the range 1 to 15 kbar revealed well-defined dislocation arrays surrounding the voids. Fig. 1 shows typical plastic regions in the vicinity of two cavities after pressurization at 3.5 kbar. Preliminary chemical polishing and etching experiments have shown these regions to consist of dislocation loops emanating from the cavity edges on six pairs of $\{110\}$ slip planes; the spacing between pairs being determined by the orthogonal cavity diagonal. When viewed in a

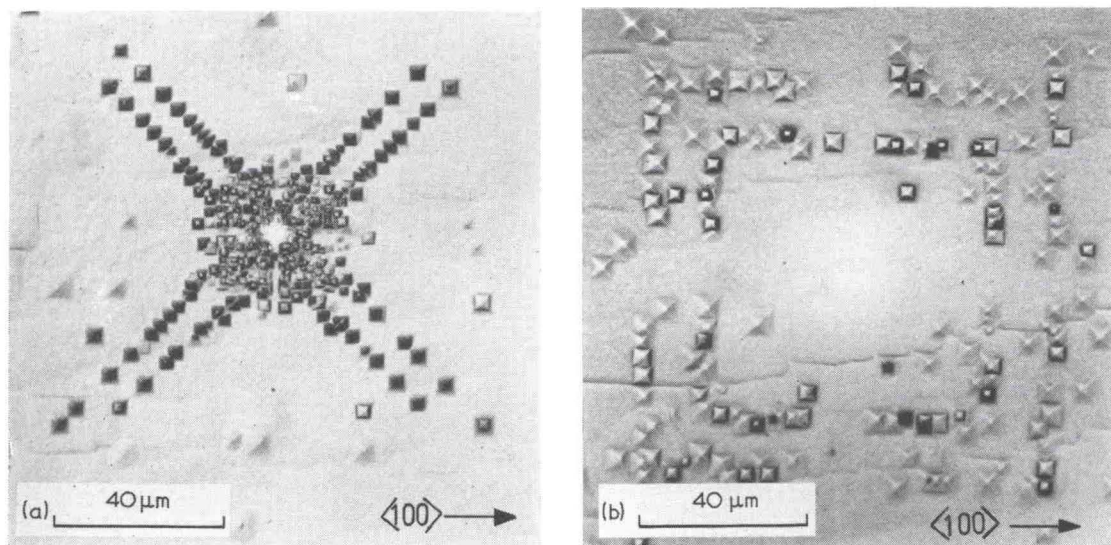


Figure 1 Well-defined dislocation arrays on $\langle 110 \rangle$ $\{110\}$ about approximately cubical cavities in a LiF single crystal pressurized at 3.5 kbar. The cavities, face diagonals approximately $10 \mu\text{m}$, were situated 10 and $40 \mu\text{m}$ below the surface in (a) and (b) respectively. Note that (a) and (b) respectively illustrate, principally the edge and screw components of the arrays.